

Description

The PDNM6N30V4A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a load switch or in PWM applications.

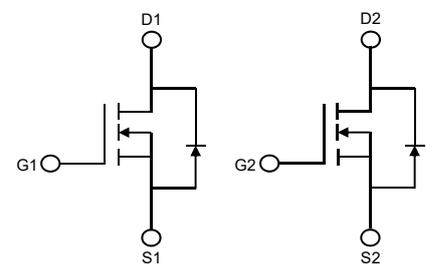
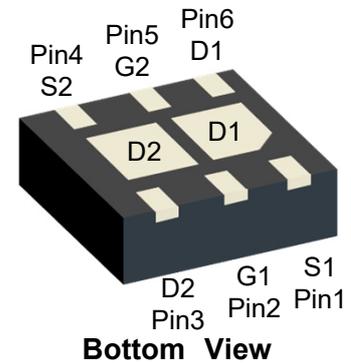
MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
30	32@ $V_{GS} = 10V$	4.0

Feature

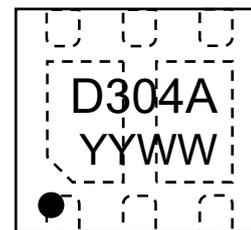
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Applications

- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	4.0	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	20	A
Total Power Dissipation	P_D	0.75	W
Avalanche Current ⁽²⁾	I_{AS}	13	A
Avalanche Energy ⁽²⁾	E_{AS}	8.6	mJ
Thermal Resistance , Junction-case ⁽³⁾	$R_{\theta JC}$	75.6	°C/W
Thermal Resistance Junction-to-Ambient ⁽³⁾	$R_{\theta JA}$	16.2	°C/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.6	2.4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3.6A$	-	32	38	m Ω
		$V_{GS} = 4.5V, I_D = 2A$	-	44	65	
Dynamic Characteristics⁴⁾						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	279	-	pF
Output Capacitance	C_{oss}		-	38	-	
Reverse Transfer Capacitance	C_{rss}		-	27	-	
Switching Characteristics⁴⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 15V, V_{GS} = 10V,$ $R_G = 10\Omega, I_D = 3.6A$	-	2.7	-	ns
Turn-on Rise Time	t_r		-	3.0	-	
Turn-Off Delay Time	$t_{d(off)}$		-	11.8	-	
Turn-Off Fall Time	t_f		-	4.3	-	
Total Gate Charge	Q_g	$V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 3.6A$	-	5.3	-	nC
Gate-Source Charge	Q_{gs}		-	0.8	-	
Gate-Drain Charge	Q_{gd}		-	1.0	-	
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$	-	-	1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^\circ C$).
2. This single-pulse measurement was taken under the following condition ($L=100\mu H, V_{GS}=30V, V_{DS}=10V$)while it's value is limited by $T_{J_Max}=150^\circ C$.
3. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
4. Guaranteed by design, not subject to production.

Typical Characteristics

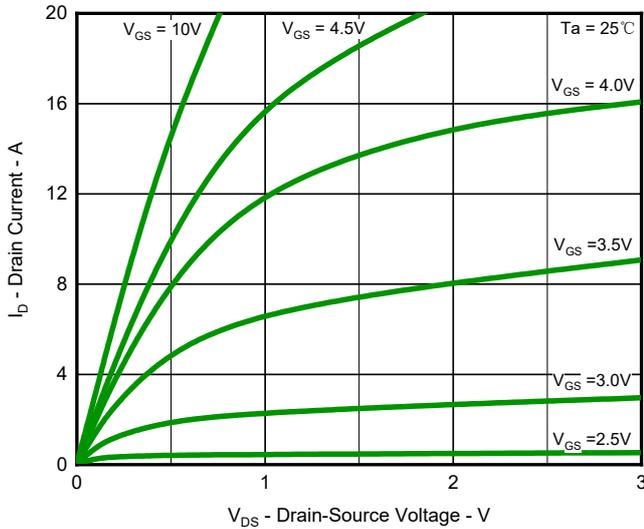


Fig.1 Output Characteristics

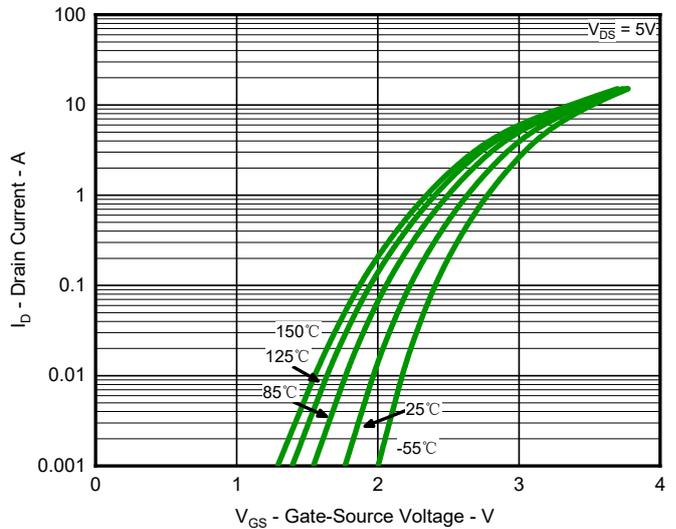


Fig.2 Typical Transfer Characteristic

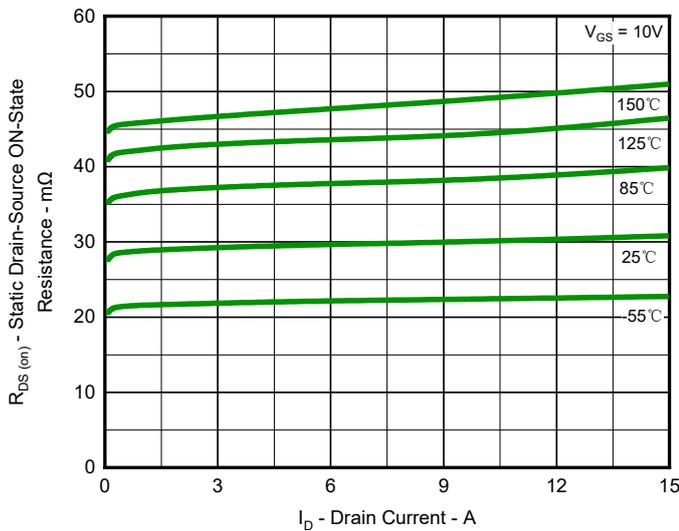


Fig.3 Typical On-Resistance vs Drain Current and Temperature

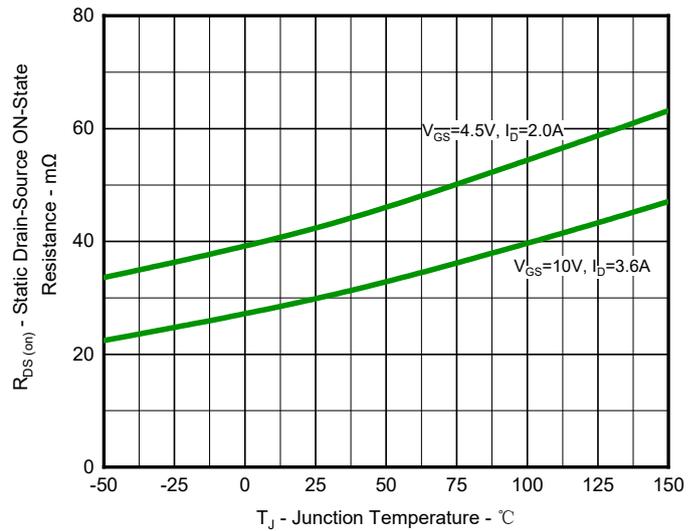


Fig.4 On-Resistance Variation with Temperature

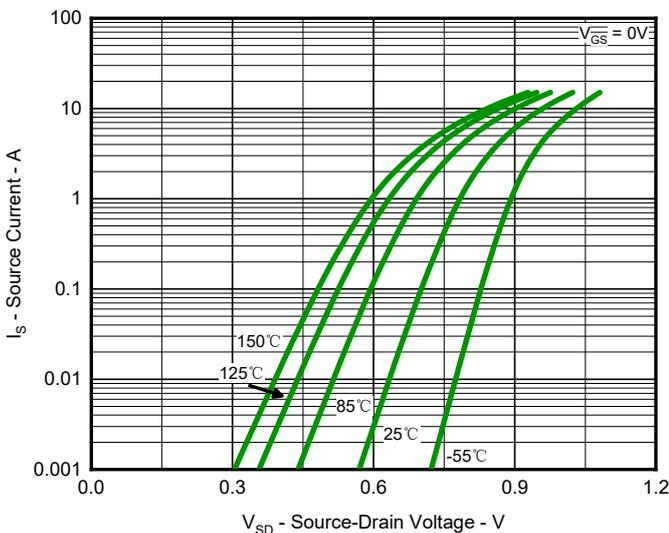


Fig.5 Diode Forward Voltage vs. Current

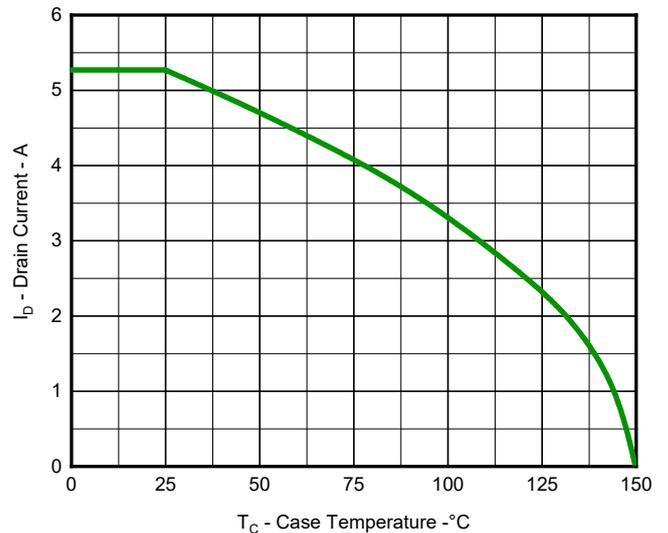


Fig.6 Maximum Drain Current vs. Case Temperature

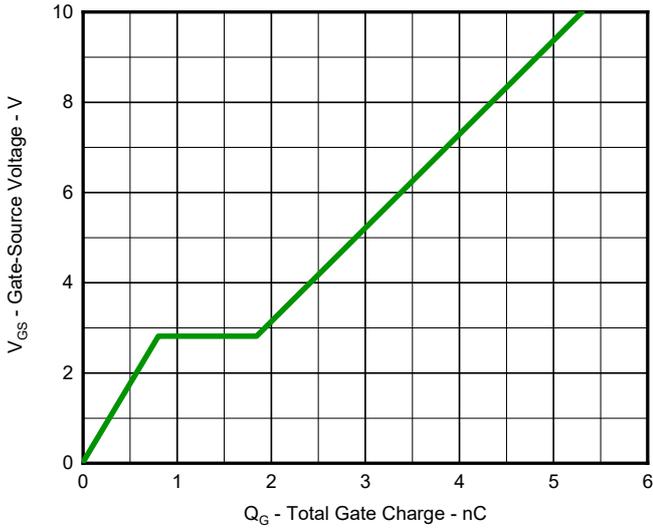


Fig.7 Gate Charge Characteristics

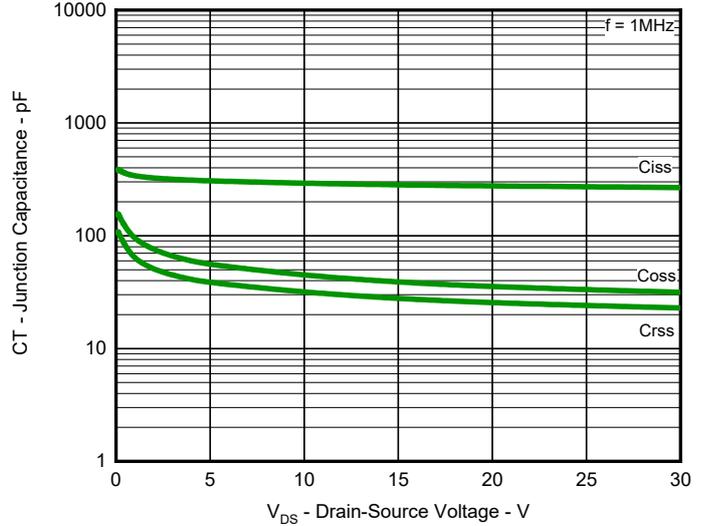


Fig.8 Typical Junction Capacitance

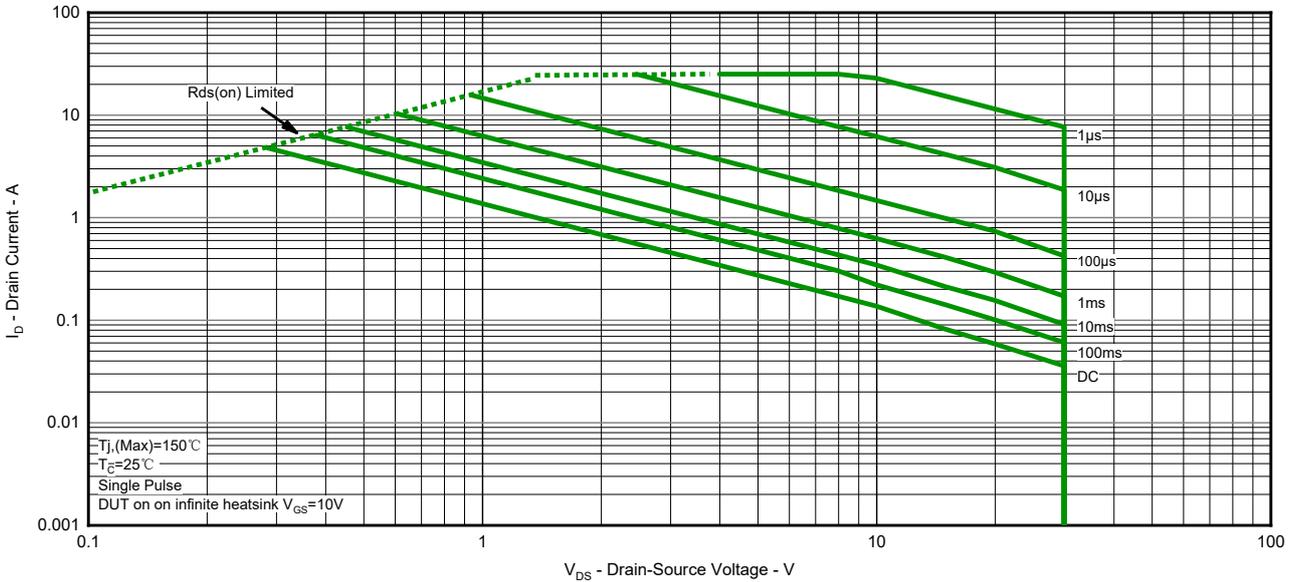


Fig.9 Safe Operation Area

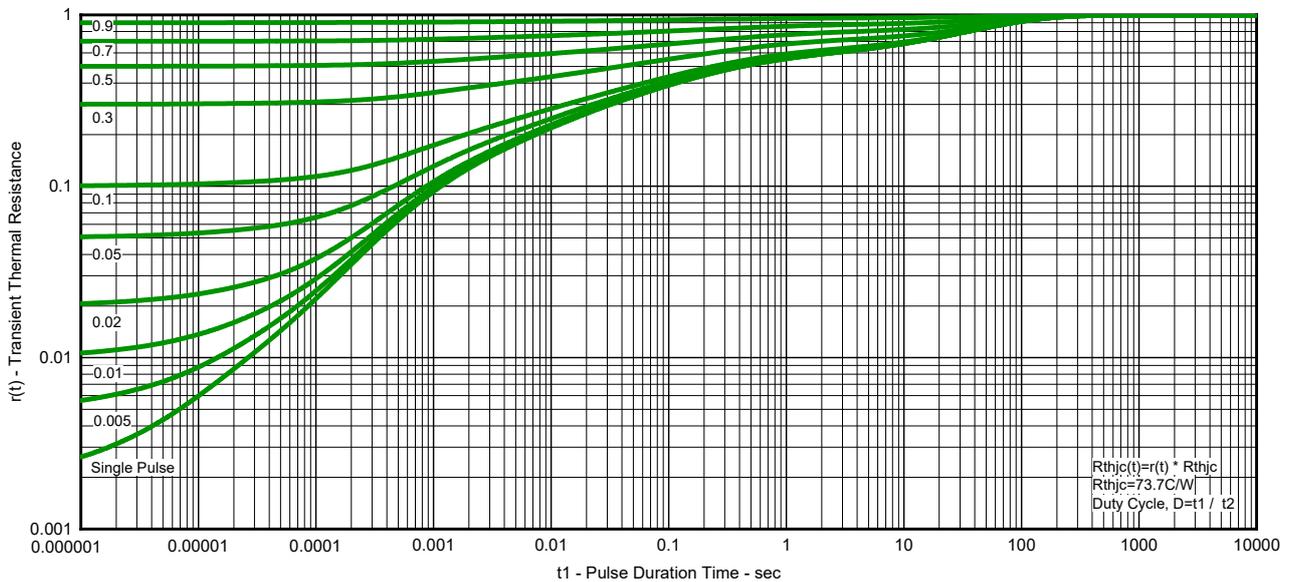
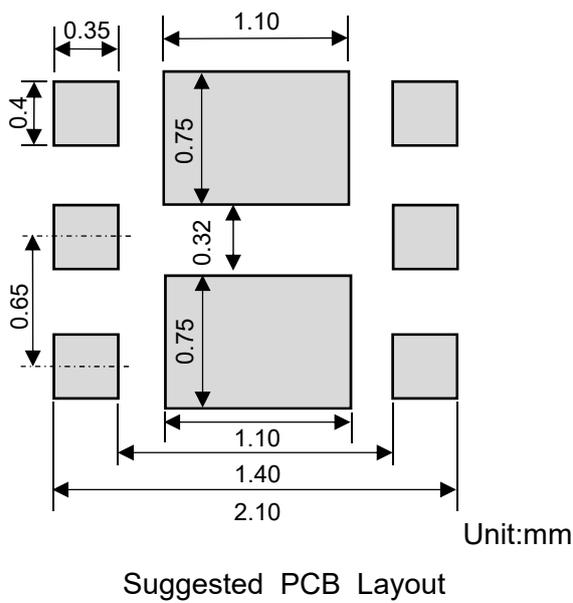
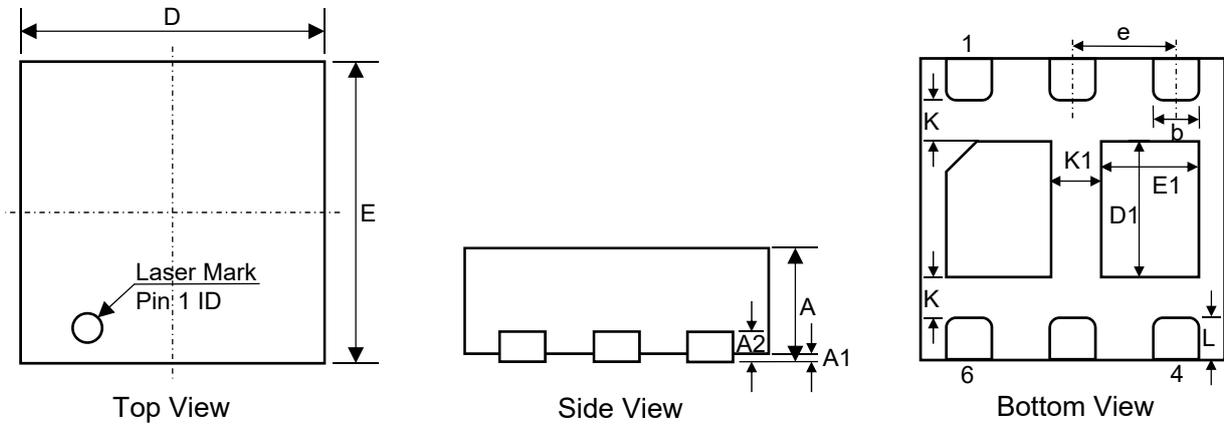


Fig.10 Transient Thermal Resistance

Product Dimension (DFN2020-6L)



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.70	0.80	0.028	0.031
A1	0.00	0.05	0.000	0.002
A2	0.203 Ref.		0.008 Ref.	
b	0.25	0.35	0.010	0.014
D	1.90	2.10	0.075	0.083
D1	0.90	1.10	0.035	0.043
E	1.90	2.10	0.075	0.083
E1	0.52	0.72	0.020	0.028
e	0.65 Typ.		0.026 Typ.	
K	0.25 Ref.		0.010 Ref.	
K1	0.32 Ref.		0.013 Ref.	
L	0.20	0.30	0.008	0.012

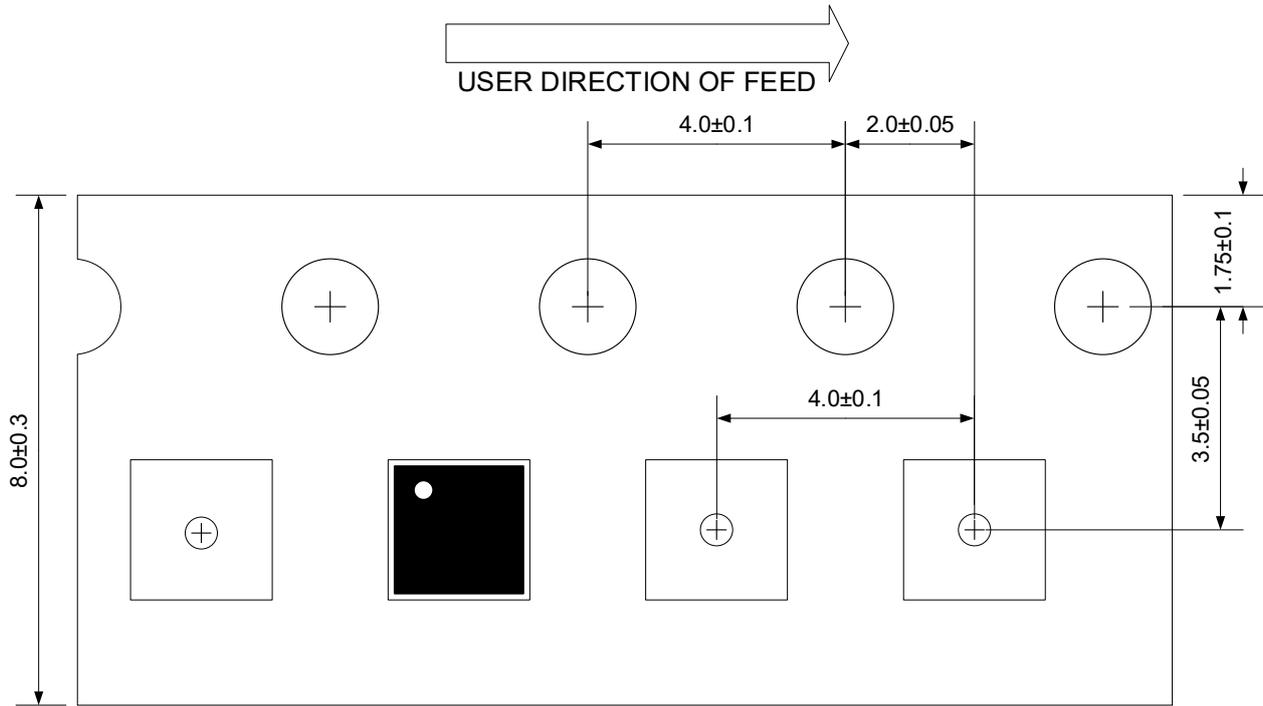
N-Channel MOSFET

PDNM6N30V4A

Ordering Information

Device	Package	Reel	Shipping
PDNM6N30V4A	DFN2020-6L (Pb-Free)	7"	3000 / Tape & Reel

Load With Information



Unit:mm

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